HD74ALVCH16260

12-bit to 24-bit Multiplexed D-type Latches with 3-state Outputs

HITACHI

ADE-205-135A (Z)
2nd. Edition
September 1997

Description

The HD74ALVCH16260 is a 12-bit to 24-bit multiplexed D-type latch used in applications where two separate data paths must be multiplexed onto, or demultiplexed from, a single data path. Typical applications include multiplexing and / or demultiplexing of address and data information in microprocessor or bus interface applications. This device is also useful in memory interleaving applications. Three 12-bit I / O ports (A1-A12, 1B1-1B12, and 2B1-2B12) are available for address and / or data transfer. The output enable ($\overline{OE1B}$, $\overline{OE2B}$, and $\overline{OEA}$) inputs control the bus transceiver functions. The $\overline{OE1B}$ and $\overline{OE2B}$ control signals also allow bank control in the A-to-B direction. Address and / or data information can be stored using the internal storage latches. The latch enable (LE1B, LE2B, LEA1B, and LEA2B) inputs are used to control data storage. When the latch enable input is high, the latch is transparent. When the latch enable input goes low, the data present at the inputs is latched and remains latched until the latch enable input is returned high. Active bus hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

Features

- V_{CC} = 2.3 V to 3.6 V
- Typical V_{OL} ground bounce < 0.8 V (@V_{CC} = 3.3 V, Ta = 25°C)
- Typical V_{OH} undershoot > 2.0 V (@V_{CC} = 3.3 V, Ta = 25°C)
- High output current ±24 mA (@V_{CC} = 3.0 V)
- Bus hold on data inputs eliminates the need for external pullup / pulldown resistors

Function Table

Inputs						Output A
1B	**2B**	**SEL**	**LE1B**	**LE2B**	$\overline{OEA}$	
H	X	H	H	X	L	H
L	X	H	H	X	L	L
X	X	H	L	X	L	A_0 *1
X	H	L	X	H	L	H
X	L	L	X	H	L	L
X	X	L	X	L	L	A_0 *1
X	X	X	X	X	H	Z

B-to-A ($\overline{OEB}$ = H)

Inputs					Outputs	
A	**LEA1B**	**LEA2B**	$\overline{OE1B}$	$\overline{OE2B}$	**1B**	**2B**
H	H	H	L	L	H	H
L	H	H	L	L	L	L
H	H	L	L	L	H	$2B_0$ *1
L	H	L	L	L	L	$2B_0$ *1
H	L	H	L	L	$1B_0$ *1	H
L	L	H	L	L	$1B_0$ *1	L
X	L	L	L	L	$1B_0$ *1	$2B_0$ *1
X	X	X	H	H	Z	Z
X	X	X	L	H	Active	Z
X	X	X	H	L	Z	Active
X	X	X	L	L	Active	Active

A-to-B ($\overline{OEA}$ = H)

H : High level

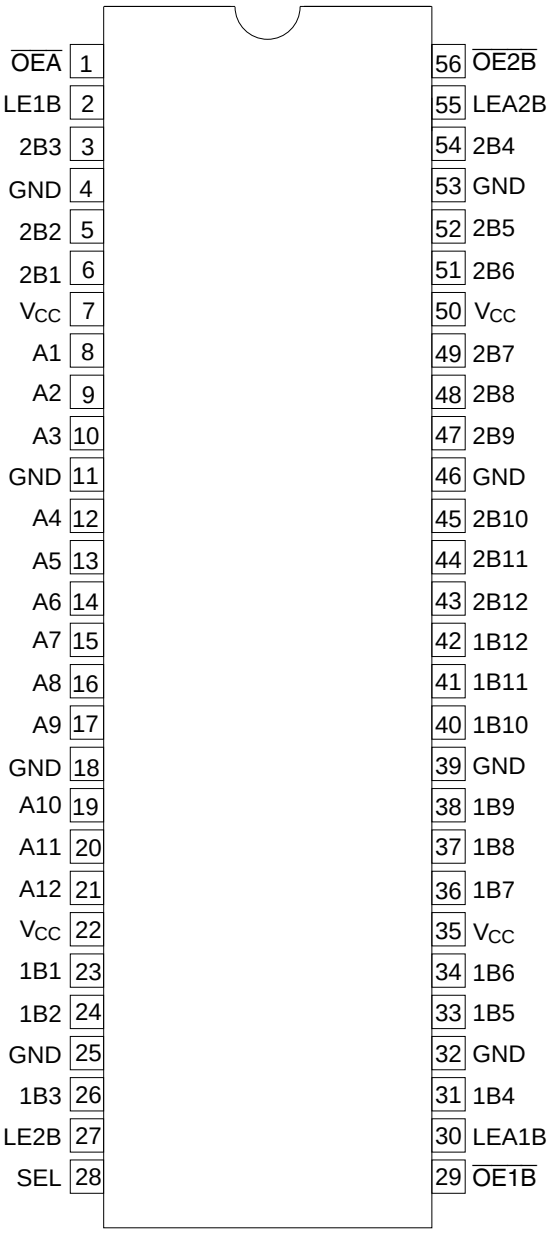
L : Low level

X : Immaterial

Z : High impedance

Note: 1. Output level before the indicated steady state input conditions were established.

Pin Arrangement



(Top view)

Absolute Maximum Ratings

Item	Symbol	Ratings	Unit	Conditions
Supply voltage	V_{CC}	–0.5 to 4.6	V	
Input voltage [*1, 2]	V_I	–0.5 to 4.6	V	Except I/O ports
		–0.5 to V_{CC} +0.5		I/O ports
Output voltage [*1, 2]	V_O	–0.5 to V_{CC} +0.5	V	
Input clamp current	I_{IK}	–50	mA	$V_I < 0$
Output clamp current	I_{OK}	±50	mA	$V_O < 0$ or $V_O > V_{CC}$
Continuous output current	I_O	±50	mA	V_O = 0 to V_{CC}
V_{CC}, GND current / pin	I_{CC} or I_{GND}	±100	mA	
Maximum power dissipation at Ta = 55°C (in still air) [*3]	P_T	1	W	TSSOP
Storage temperature	Tstg	–65 to 150	°C	

Notes: Stresses beyond those listed under “absolute maximum ratings” may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under “recommended operating conditions” is not implied. Exposure to absolute maximum rated conditions for extended periods may affect device reliability.

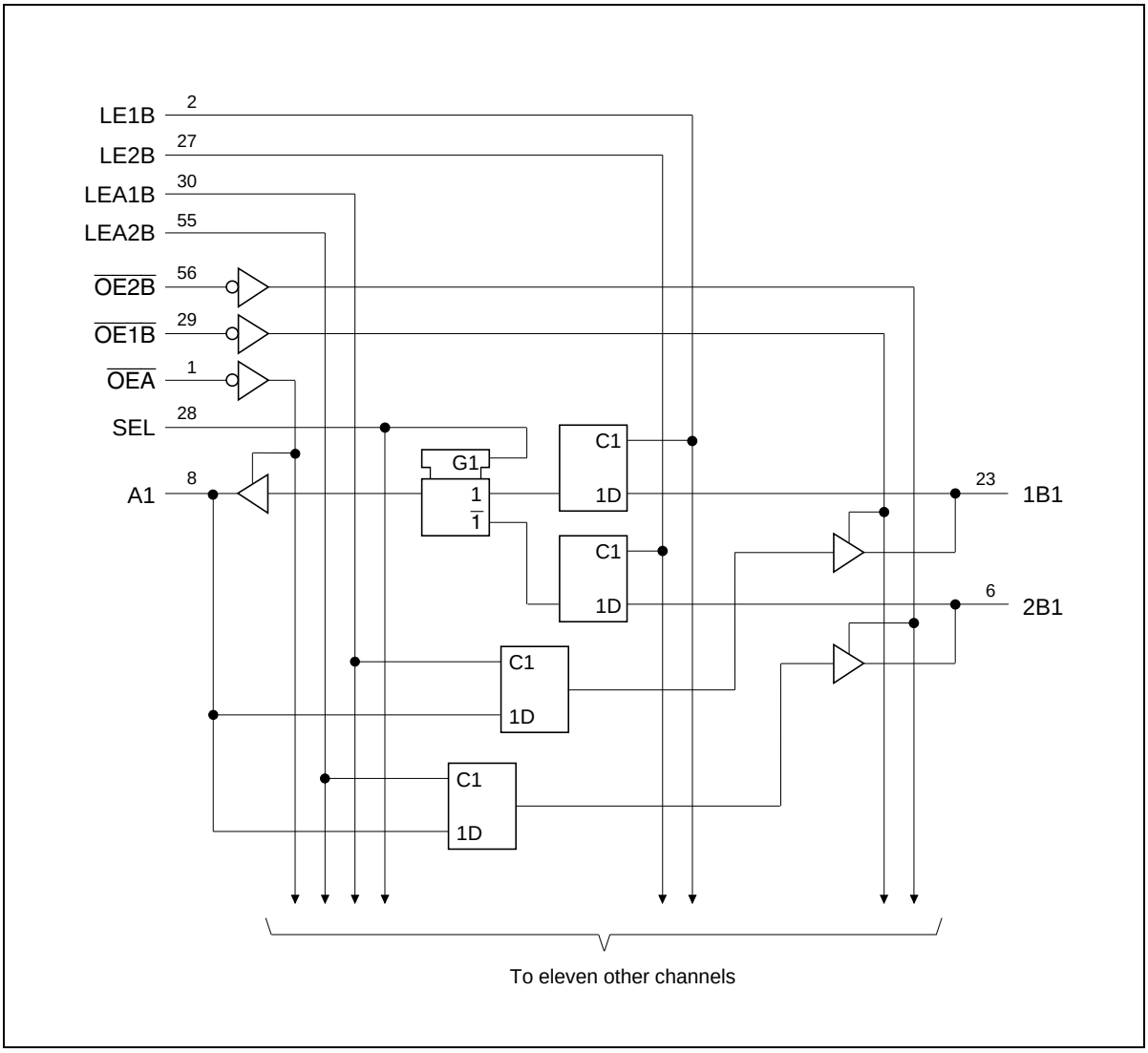
1. The input and output negative voltage ratings may be exceeded if the input and output clamp current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils.

Recommended Operating Conditions

Item	Symbol	Min	Max	Unit	Conditions
Supply voltage	V_{CC}	2.3	3.6	V	
Input voltage	V_I	0	V_{CC}	V	
Output voltage	V_O	0	V_{CC}	V	
High level output current	I_{OH}	—	–12	mA	V_{CC} = 2.3 V
		—	–12		V_{CC} = 2.7 V
		—	–24		V_{CC} = 3.0 V
Low level output current	I_{OL}	—	12	mA	V_{CC} = 2.3 V
		—	12		V_{CC} = 2.7 V
		—	24		V_{CC} = 3.0 V
Input transition rise or fall rate	Æt / Æv	0	10	ns / V	
Operating temperature	Ta	–40	85	°C	

Note: Unused control inputs must be held high or low to prevent them from floating.

Logic Diagram



Electrical Characteristics (Ta = –40 to 85°C)

Item	Symbol	V_{CC} (V) [*1]	Min	Max	Unit	Test Conditions
Input voltage	V_{IH}	2.3 to 2.7	1.7	—	V	
		2.7 to 3.6	2.0	—		
	V_{IL}	2.3 to 2.7	—	0.7		
		2.7 to 3.6	—	0.8		
Output voltage	V_{OH}	Min to Max	V_{CC}–0.2	—	V	I_{OH} = –100 µA
		2.3	2.0	—		I_{OH} = –6 mA, V_{IH} = 1.7 V
		2.3	1.7	—		I_{OH} = –12 mA, V_{IH} = 1.7 V
		2.7	2.2	—		I_{OH} = –12 mA, V_{IH} = 2.0 V
		3.0	2.4	—		I_{OH} = –12 mA, V_{IH} = 2.0 V
		3.0	2.0	—		I_{OH} = –24 mA, V_{IH} = 2.0 V
	V_{OL}	Min to Max	—	0.2		I_{OL} = 100 µA
		2.3	—	0.4		I_{OL} = 6 mA, V_{IL} = 0.7 V
		2.3	—	0.7		I_{OL} = 12 mA, V_{IL} = 0.7 V
		2.7	—	0.4		I_{OL} = 12 mA, V_{IL} = 0.8 V
		3.0	—	0.55		I_{OL} = 24 mA, V_{IL} = 0.8 V
Input current	I_{IN}	3.6	—	±5	µA	V_{IN} = V_{CC} or GND
	$I_{IN (hold)}$	2.3	45	—		V_{IN} = 0.7 V
		2.3	–45	—		V_{IN} = 1.7 V
		3.0	75	—		V_{IN} = 0.8 V
		3.0	–75	—		V_{IN} = 2.0 V
		3.6	—	±500		V_{IN} = 0 to 3.6 V
Off state output current [*2]	I_{OZ}	3.6	—	±10	µA	V_{OUT} = V_{CC} or GND
Quiescent supply current	I_{CC}	3.6	—	40	µA	V_{IN} = V_{CC} or GND
	ΔI_{CC}	3.0 to 3.6	—	750	µA	V_{IN} = one input at (V_{CC}–0.6) V, other inputs at V_{CC} or GND

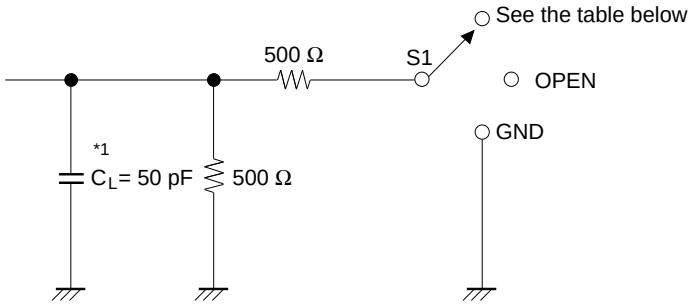
Notes: 1. For conditions shown as Min or Max, use the appropriate values under recommended operating conditions.

2. For I/O ports, the parameter I_{OZ} includes the input leakage current.

Switching Characteristics (Ta = –40 to 85°C)

Item	Symbol	V_{cc} (V)	Min	Typ	Max	Unit	FROM (Input)	TO (Output)
Maximum clock frequency	f_{max}	2.5±0.2	150	—	—	MHz		
		2.7	150	—	—			
		3.3±0.3	150	—	—			
Propagation delay time	t_{PLH}	2.5±0.2	1.2	—	6.0	ns	A or B	B or A
	t_{PHL}	2.7	—	—	5.1			
		3.3±0.3	1.2	—	4.3			
		2.5±0.2	1.0	—	6.2		$\overline{LE}$	A or B
		2.7	—	—	5.2			
		3.3±0.3	1.0	—	4.4			
		2.5±0.2	1.2	—	7.5		SEL	A
		2.7	—	—	6.6			
		3.3±0.3	1.1	—	5.6			
Output enable time	t_{ZH}	2.5±0.2	1.0	—	7.2	ns	$\overline{OE}$	A or B
	t_{ZL}	2.7	—	—	6.4			
		3.3±0.3	1.0	—	5.4			
Output disable time	t_{HZ}	2.5±0.2	1.7	—	5.9	ns	$\overline{OE}$	A or B
	t_{LZ}	2.7	—	—	5.0			
		3.3±0.3	1.3	—	4.6			
Setup time	t_{su}	2.5±0.2	1.4	—	—	ns		
		2.7	1.1	—	—			
		3.3±0.3	1.1	—	—			
Hold time	t_h	2.5±0.2	1.6	—	—	ns		
		2.7	1.9	—	—			
		3.3±0.3	1.5	—	—			
Pulse width	t_w	2.5±0.2	3.3	—	—	ns		
		2.7	3.3	—	—			
		3.3±0.3	3.3	—	—			
Input capacitance	C_{IN}	3.3	—	3.5	—	pF	Control inputs	
Output capacitance	$C_{IN/O}$	3.3	—	9.0	—	pF	A or B ports	

• **Test Circuit**

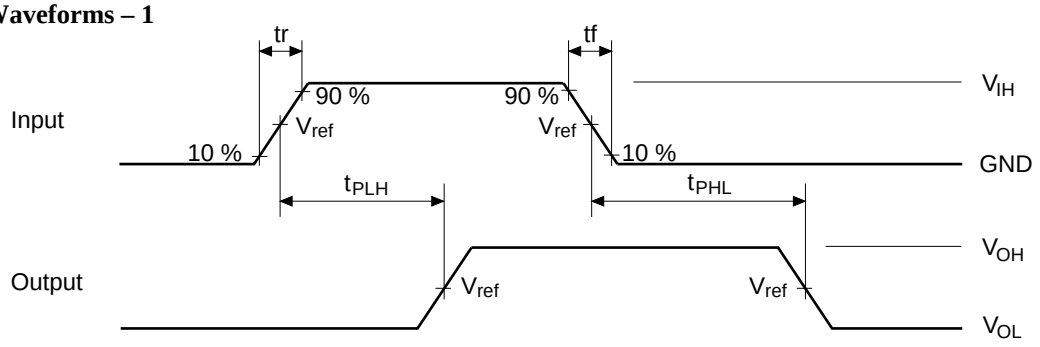


Load Circuit for Outputs

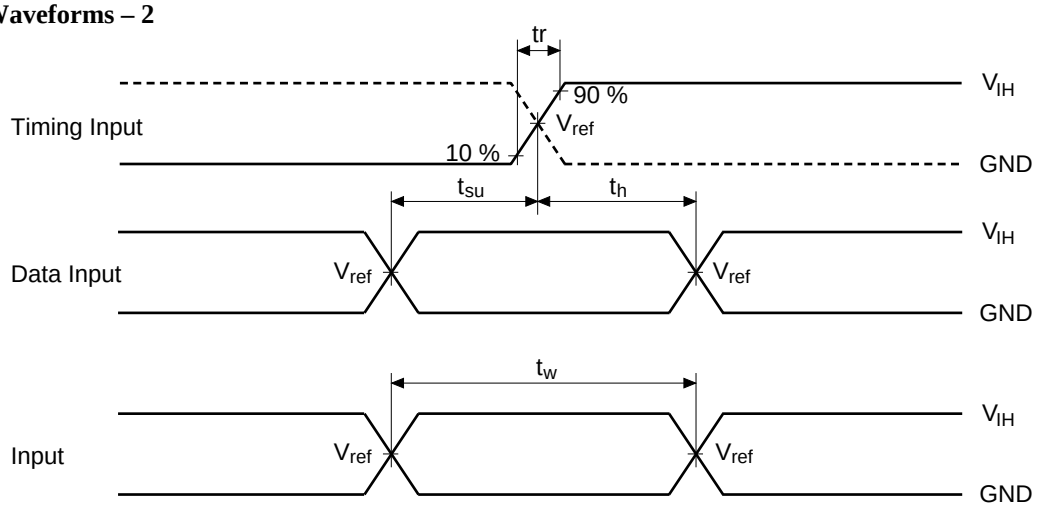
Symbol	Vcc=2.5±0.2V	Vcc=2.7V, 3.3±0.3V
t_{PLH}/ t_{PHL}	OPEN	OPEN
t_{su} / t_h / t_w		
t_{ZH}/ t_{HZ}	GND	GND
t_{ZL} / t_{LZ}	4.6 V	6.0 V

Note: 1. C_L includes probe and jig capacitance.

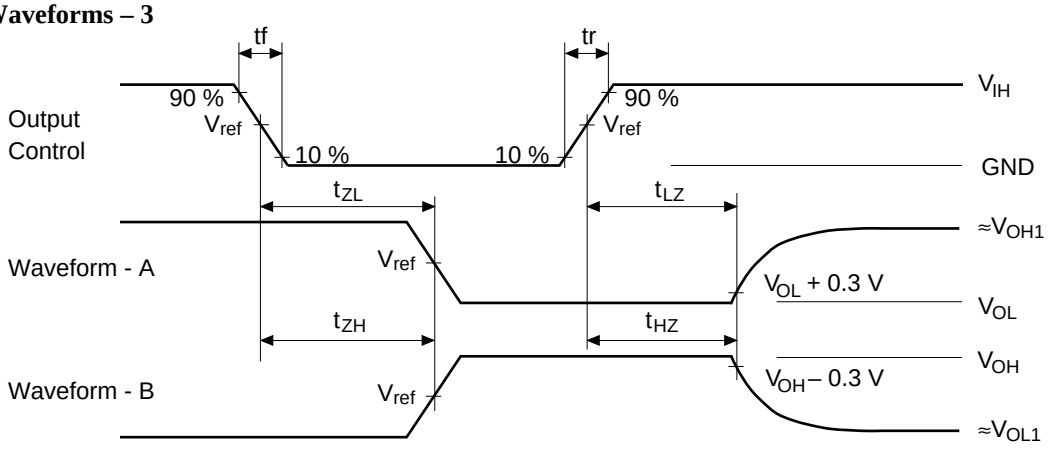
• **Waveforms – 1**



• **Waveforms – 2**



• **Waveforms – 3**

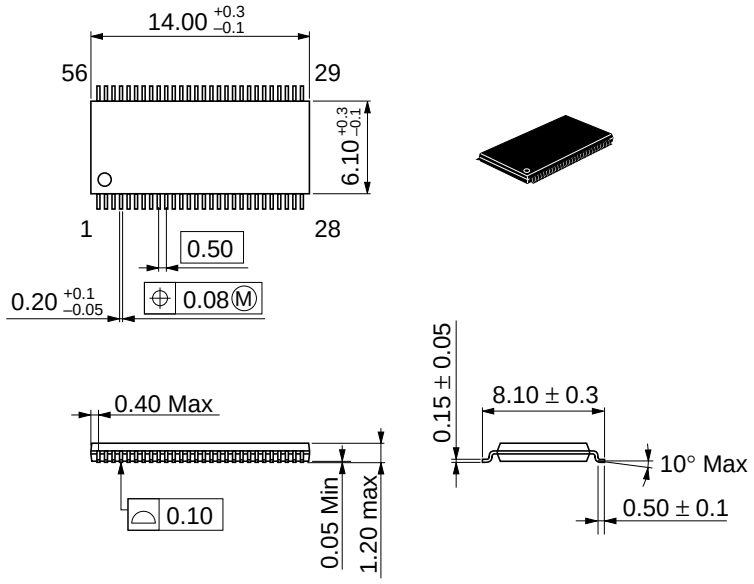


TEST	Vcc=2.5±0.2V	Vcc=2.7V, 3.3±0.3V
V_{IH}	2.3 V	2.7 V
V_{ref}	1.2 V	1.5 V
V_{OH1}	2.3 V	3.0 V
V_{OL1}	GND	GND

Notes: 1. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Zo = 50 Ω, tr ≤ 2.5 ns, tf ≤ 2.5 ns.
2. Waveform – A is for an output with internal conditions such that the output is low except when disabled by the output control.
3. Waveform – B is for an output with internal conditions such that the output is high except when disabled by the output control.
4. The output are measured one at a time with one transition per measurement.

Package Dimensions

Unit : mm



Hitachi code	TTP-56D
EIAJ code	—
JEDEC code	—

When using this document, keep the following in mind:

1. This document may, wholly or partially, be subject to change without notice.
2. All rights are reserved: No one is permitted to reproduce or duplicate, in any form, the whole or part of this document without Hitachi's permission.
3. Hitachi will not be held responsible for any damage to the user that may result from accidents or any other reasons during operation of the user's unit according to this document.
4. Circuitry and other examples described herein are meant merely to indicate the characteristics and performance of Hitachi's semiconductor products. Hitachi assumes no responsibility for any intellectual property claims or other problems that may result from applications based on the examples described herein.
5. No license is granted by implication or otherwise under any patents or other rights of any third party or Hitachi, Ltd.
6. MEDICAL APPLICATIONS: Hitachi's products are not authorized for use in MEDICAL APPLICATIONS without the written consent of the appropriate officer of Hitachi's sales company. Such use includes, but is not limited to, use in life support systems. Buyers of Hitachi's products are requested to notify the relevant Hitachi sales offices when planning to use the products in MEDICAL APPLICATIONS.

HITACHI

Hitachi, Ltd.
Semiconductor & IC Div.
Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100, Japan
Tel: Tokyo (03) 3270-2111
Fax: (03) 3270-5109

For further information write to:

Hitachi America, Ltd.
Semiconductor & IC Div.
2000 Sierra Point Parkway
Brisbane, CA. 94005-1835
U S A
Tel: 415-589-8300
Fax: 415-583-4207

Hitachi Europe GmbH
Continental Europe
Dornacher Straße 3
D-85622 Feldkirchen
München
Tel: 089-9 91 80-0
Fax: 089-9 29 30-00

Hitachi Europe Ltd.
Electronic Components Div.
Northern Europe Headquarters
Whitebrook Park
Lower Cookham Road
Maidenhead
Berkshire SL6 8YA
United Kingdom
Tel: 01628-585000
Fax: 01628-585160

Hitachi Asia Pte. Ltd.
16 Collyer Quay #20-00
Hitachi Tower
Singapore 049318
Tel: 535-2100
Fax: 535-1533

Hitachi Asia (Hong Kong) Ltd.
Unit 706, North Tower,
World Finance Centre,
Harbour City, Canton Road
Tsim Sha Tsui, Kowloon
Hong Kong
Tel: 27359218
Fax: 27306071